## G LAKSHMI PRIYA

- G Lakshmi Priya, Balamurugan N B, Improvement of Subthreshold Characteristics of Dopingless Tunnel FET Using Hetero Gate Dielectric Material: Analytical Modeling and Simulation, Journal Silicon, Pages 1-13, Springer(2019)
- Balamurugan N B Lakshmi Priya G, New dual material double gate junctionless tunnel FET: Subthreshold modeling and simulation, International Journal of Electronics and Communication, Volume 99, Pages 130-138(2019)
- N B Balamurugan G Lakshmi Priya, Subthreshold Modeling of Triple Material Gate-All-Around Junctionless Tunnel FET with Germanium and High-K Gate Dielectric Material, Informacije Midem-Journal of Microelectronics Electronic Components and Materials, Volume 48, Issue 1, Pages 53-61(2018)
- 4. P Vanitha, NB Balamurugan, G Lakshmi Priya, Triple material surrounding gate (TMSG) nanoscale tunnel FET-analytical modeling and simulation, Journal of Semiconductor Technology and science Volume 15,Issue 6, Pages 585-593(2015)
- 5. S Theodore Chandra, NB Balamurugan, G Lakshmi Priya, S Manikandan, Subthreshold behavior of AlInSb/InSb high electron mobility transistor, IOP Publishing, Volume 24,Issue 7,Pages 076105 (2015)
- D Saraswathi, NB Balamurugan, G Lakshmi Priya, S Manikandan, A compact analytical model for 2D triple material surrounding gate nanowire tunnel field effect transistors, Intelligent Computing and Applications, Pages 325-332, Springer, New Delhi(2015)
- G Lakshmi Priya, NB Balamurugan, Triple Material Gate Work Function Engineering in Surrounding Gate Nanoscale MOSFETs for reduced Short Channel Effects (SCE's): Scale Length Model, International Journal of ChemTech Research, Volume 7, Issue 2,Pages 1005-10113(2015)